

INTERNATIONAL STANDARD



**Semiconductor devices – Mechanical and climatic test methods –
Part 28: Electrostatic discharge (ESD) sensitivity testing – Charged device
model (CDM) – device level**



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INTERNATIONAL ELECTROTECHNICAL COMMISSION

**SEMICONDUCTOR DEVICES –
MECHANICAL AND CLIMATIC TEST METHODS –****Part 28: Electrostatic discharge (ESD) sensitivity testing –
Charged device model (CDM) – device level**

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This standard is based on ESDA/JEDEC Joint Standard ANSI/ESDA/JEDEC JS-002 which resulted from the merging of JESD22-C101 and ANSI/ESD S5.3.1). It contains the essential elements from both standards. The co-operation of ANSI/ESDA/JEDEC is gratefully acknowledged.

The text of this International Standard is based on the following documents:

FDIS	Report on voting
47/2362/FDIS	47/2379/RVD

Full information on the voting for the approval of this International Standard can be found in the report on voting indicated in the above table.

This document has been drafted in accordance with the ISO/IEC Directives, Part 2.

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INTRODUCTION

The earliest electrostatic discharge (ESD) test models and standards simulate a charged object approaching a device and discharging through the device. The most common example is IEC 60749-26, the human body model (HBM). However, with the increasing use of automated device handling systems, another potentially destructive discharge mechanism, the charged device model (CDM), becomes increasingly important. In the CDM, a device itself becomes charged (e.g. by sliding on a surface (tribocharging) or by electric field induction) and is rapidly discharged (by an ESD event) as it closely approaches a conductive object. A critical feature of the CDM is the metal-metal discharge, which results in a very rapid transfer of charge through an air breakdown arc. The CDM test method also simulates metal-metal discharges arising from other similar scenarios, such as the discharging of charged metal objects to devices at different potential.

Accurately quantifying and reproducing this fast metal-metal discharge event is very difficult, if not impossible, due to the limitations of the measuring equipment and its influence on the discharge event. The CDM discharge is generally completed in a few nanoseconds, and peak currents of tens of amperes have been observed. The peak current into the device will vary considerably depending on a large number of factors, including package type and parasitics. The typical failure mechanism observed in MOS devices for the CDM model is dielectric damage, although other damage has been noted.

The CDM charge voltage sensitivity of a given device is package dependent. For example, the same integrated circuit (IC) in a small area package can be less susceptible to CDM damage at a given voltage compared to that same IC in a package of the same type with a larger area. It has been shown that CDM damage susceptibility correlates better to peak current levels than charge voltage.

Without
Charge